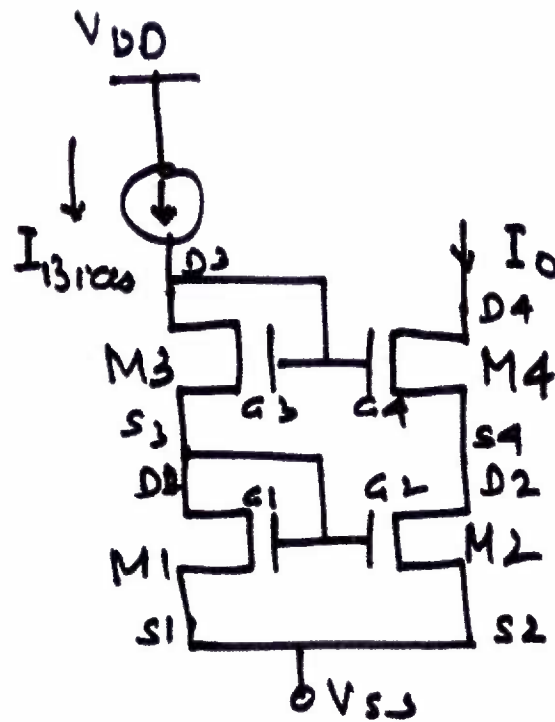


CASCODE CURRENT MIRROR



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M2 & M4 form Cascode Stage leading to Higher Rout.

However we must ensure that M2 & M4 are in Saturation. In current source case, not only we need High Rout, but very small V_{min}

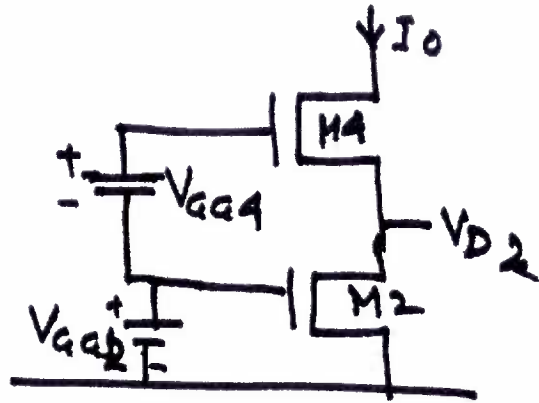
For a 5μ ($V_{DD} = 5V$) Process

$$V_{Th} \approx 0.83V \quad \& \quad V_{OV} = 0.37V$$

$$\text{i.e. } V_{GS} = 1.2V$$

V_{min} is drop across current source





If $V_{GS} = 1.2 \text{ V}$

then $V_{GG1} = V_{GG2} = 1.2$

and $V_{GG3} = V_{GG4} = 1.2 + 1.2$
 $= 2.4 \text{ V}$

For M4 in Saturation

$$V_{DS4} > V_{GS4} - V_T$$

$$\text{Now } V_{D2} = V_{S4}$$

For M2 to saturate $V_{DS2} \geq V_{GS2} - V_T$

If we keep $V_{DS2} = V_{GS2}$, then M2 is always in Saturation

$$\therefore V_{DS2} = V_{GG1} = V_{GG2} = 1.2 \text{ V}$$

For M4 to be in saturation $V_{D4} - V_{D2} \geq V_{GG4} - V_{D2} - V_T$

$$\text{or } V_{D4} \geq 2.4 - 0.83 = 1.57 \text{ V} = (2V_{OV} + V_T)$$

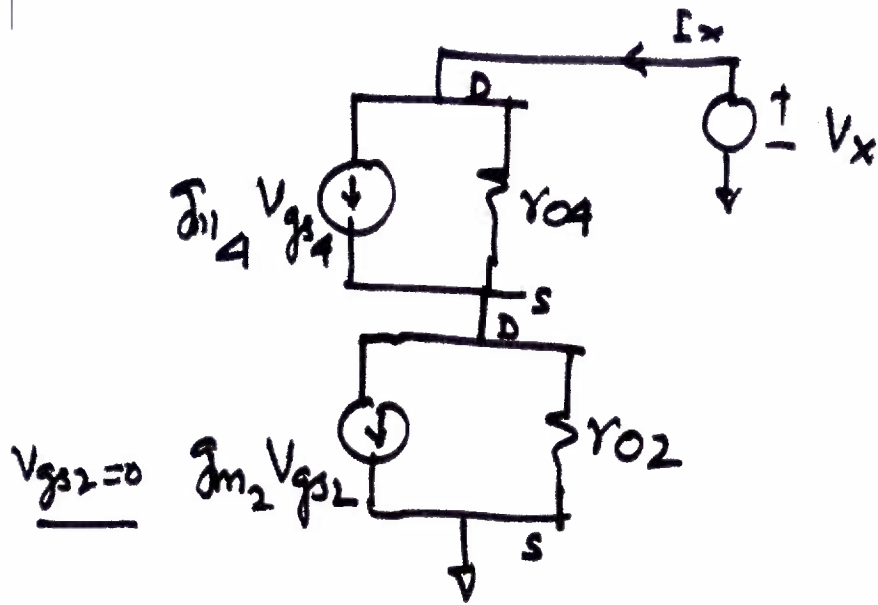
$$\text{i.e. } V_{min} \geq 2V_{OV} + V_T$$



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ROUT evaluation



$$R_{out} = r_{o4} (1 + g_{m2} r_{o2}) + r_{o2}$$

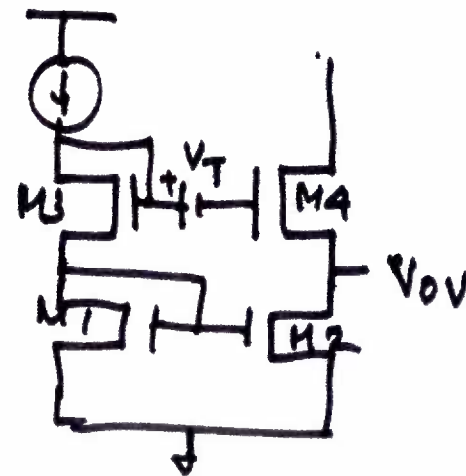
$$\approx r_{o4} (1 + g_{m2} r_{o2})$$

$$\approx g_{m4} r_{o2} r_{o4} \text{ (Cascode Effect)}$$

To reduce V_{min} , we use additional Battery of V_T between Gates of $M3$ & $M4$.

This gives $V_{G4} = 2V_{ov} + V_T$

$$\therefore V_{min} = 2V_{ov} + V_T - (V_{ov} + V_T) = V_{ov}$$



Sensitivity Analysis

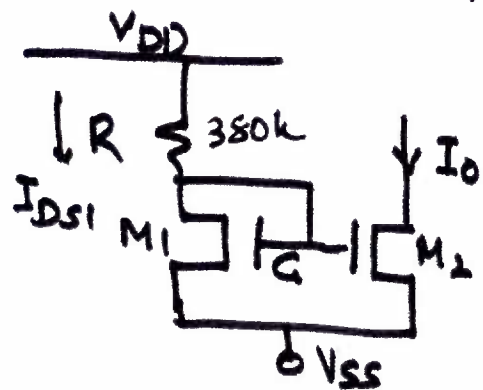
$$S_x^y = \lim_{\Delta x \rightarrow 0} \frac{\Delta y / y}{\Delta x / x} \quad \text{Definition}$$



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(i) Sensitivity of Current Source wrt V_{DD}
in a Simple Current Mirror (W/L are equal for M_1 & M_2)



We have $I_O = I_{DS1} = 10 \mu A$

However $I_{DS1} = \frac{V_{DD} - V_{SS} - V_{GS}}{R}$

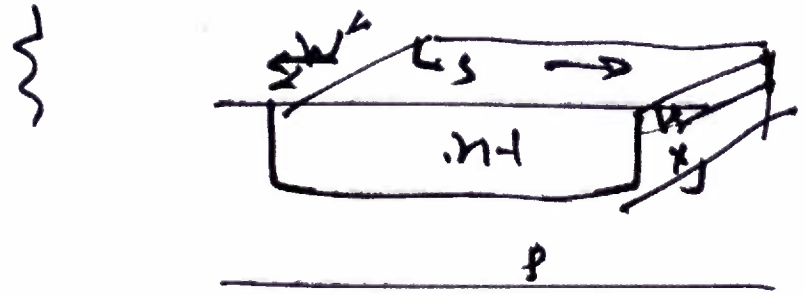
We need to find $S_{V_{DD}}^{I_O} = \lim_{\Delta V_{DD} \rightarrow 0} \frac{\Delta I_O / I_O}{\Delta V_{DD} / V_{DD}}$

$$\text{or } S_{V_{DD}}^{I_O} = \frac{V_{DD}}{I_O} \frac{\partial I_O}{\partial V_{DD}}$$

$$\text{But } \frac{\partial I_O}{\partial V_{DD}} = \frac{\partial I_{DS1}}{\partial V_{DD}} = \frac{1}{R}$$

$$\therefore S_{V_{DD}}^{I_O} = \frac{V_{DD}}{I_O R} = \frac{2.5}{10^{-5} \times 380k} \approx 0.66$$

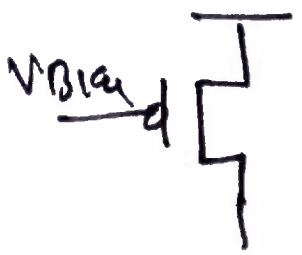
$$\Delta \frac{\Delta I_O}{I_O} = \frac{0.66 \times 0.2}{2.5} \quad (\text{if } V_{DD} \text{ becomes } V_{DD} \pm 0.1V) \approx 5\%$$



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$$R_c = R_s \cdot \frac{L}{w}$$



$$G = q \mu_n n t$$

$$R = \frac{L}{G \cdot A}$$

$$A = w \cdot L_s$$

$$t = x_j$$

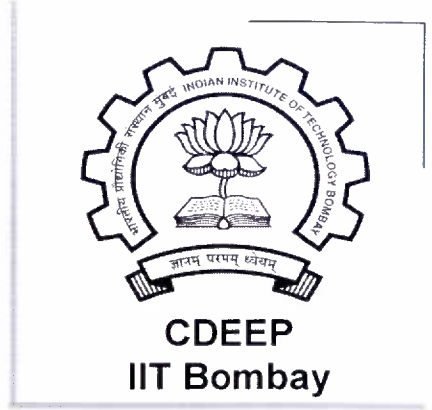
$$g = \frac{1}{q \mu_n n t}$$

$$R_s = \frac{p}{F}$$



$$1. \quad TC_f(R) = \frac{1}{R} \frac{dR}{dT} \approx +2000 \text{ ppm}/^\circ\text{C}$$

Where R is created from Diffused nt region



$$2. \quad TC_f(V_T) = -3000 \text{ ppm}/^\circ\text{C} \quad \text{for } V_T \approx 0.8\text{V}$$

Typically $\frac{\partial V_T}{\partial T} = -2.4 \text{ mV}/^\circ\text{C}$

$$3. \quad \text{For a MOSFET } \beta' = \mu C_{ox}, \therefore \beta'(T) = \beta'(0) \left(\frac{T}{T_0}\right)^{-3/2}$$

This gives $\frac{1}{\beta'} \frac{\partial \beta'}{\partial T} \approx -\frac{1.5}{T}$, T in $^\circ\text{K}$

$$\text{or } TC_f(\beta') \approx -\frac{1.5}{T} \rightarrow = \frac{1.5}{300} = \frac{1}{200} = \frac{10^6}{200} \text{ ppm}/^\circ\text{C} \\ = 5000 \text{ ppm}/^\circ\text{C}$$



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(2) Temperature Sensitivity

$$TC_f(I_0) = \frac{1}{I_0} \frac{\partial I_0}{\partial T}$$

$$S_T^{I_0} = \lim_{\Delta T \rightarrow 0} \frac{\Delta I_0 / I_0}{\Delta T / T} = \frac{T}{I_0} \frac{\partial I_0}{\partial T} = T \cdot TC_f(I_0)$$

$TC_f(I_0) \Rightarrow$ evaluation

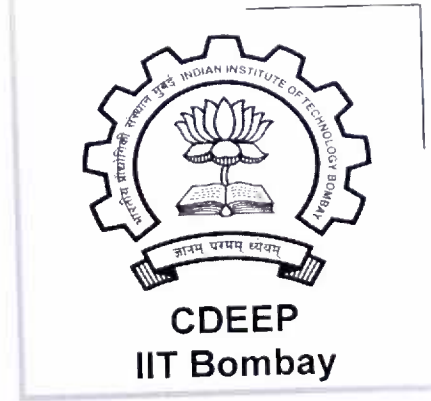
$$I_0 = I_{DS1} = \frac{V_{DD} - V_{as} - V_{ss}}{R} \quad \text{for Simple Mirror}$$

$$\frac{\partial I_0}{\partial T} = \frac{\partial I_{DS1}}{\partial T} = -\frac{1}{R} \frac{\partial V_{as}}{\partial T} + \frac{1}{R} V_{as} \frac{\partial R}{\partial T}$$

$$\therefore TC_f(I_0) = \frac{1}{I_0} \left[-\frac{1}{R} \frac{\partial V_T}{\partial T} - \frac{1}{R} \frac{\partial}{\partial T} \sqrt{\frac{2I_0 R}{\beta}} + \frac{1}{R} \frac{\partial R}{\partial T} \right]$$

Typical value

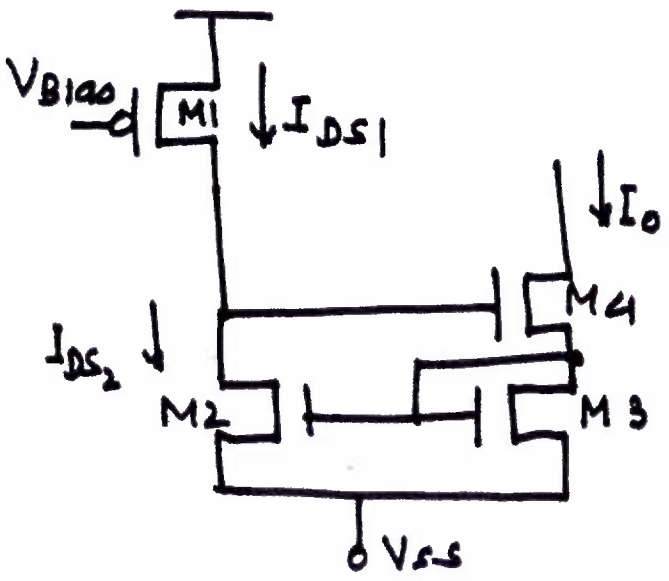
$$\begin{aligned} TC_f(I_0) &= 0.17 \% / ^\circ\text{C} = 1700 \text{ ppm}/^\circ\text{C} \\ &= 1700 \text{ ppm}/^\circ\text{C} \end{aligned}$$



Using -ve feedback, Simple Current Mirror can further be improved. Two such circuits are

- 1. Wilson Mirror
- 2. Regulated Cascode

Wilson Current Mirror:



By Using P-device with proper bias we can create stable & Reference current I_{DS1} . V_{Bias} is normally taken from a 'Stable Band Gap reference'

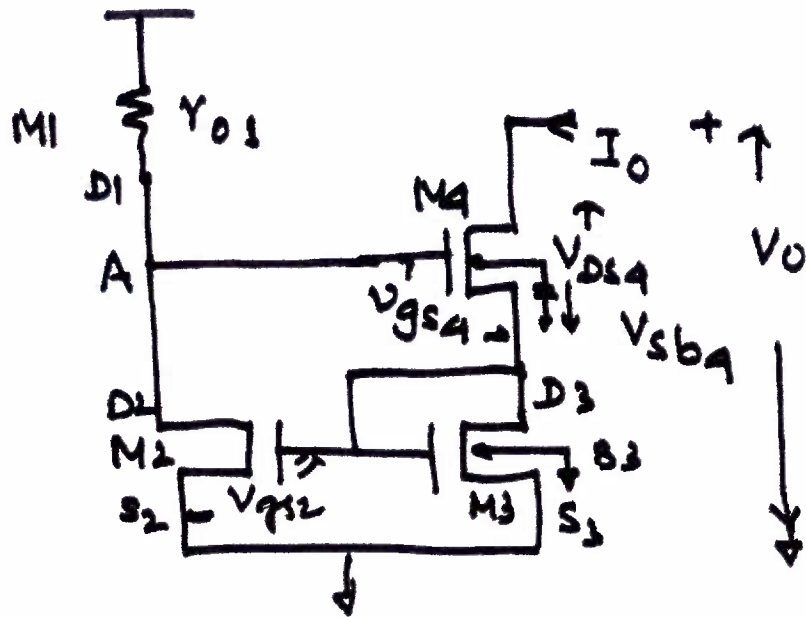
This Current Mirror has

- (i) I_O much stable than Simple Case
- (ii) Output Impedance is further improved.

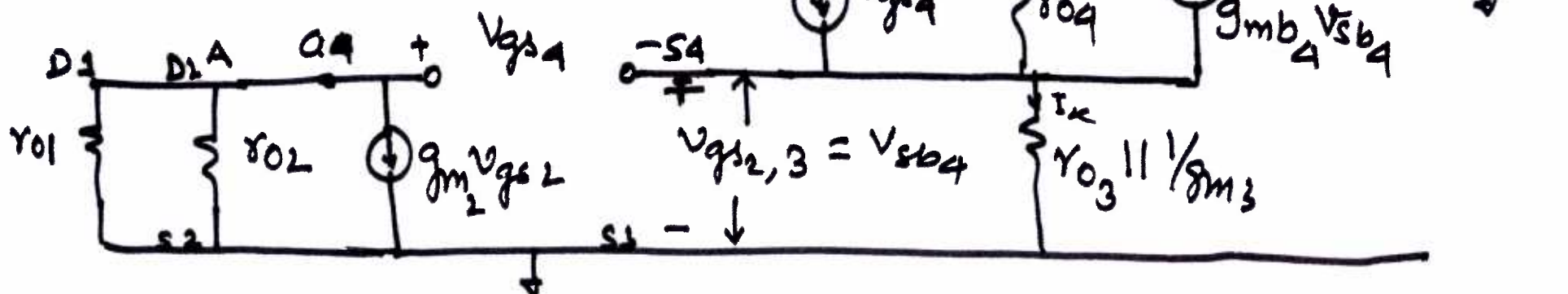


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- V_O increases
- $\rightarrow I_{DS4}$ increases
- $\rightarrow I_{DS4} = I_{DS3}$ & hence increase of I_{DS4} increases I_{DS2} .
- $\rightarrow V_A$ decreases
- $\rightarrow V_{gs4}$ decreases $\rightarrow I_{DS4} \downarrow$



$$V_{sb4} = V_{gs2} = V_{gs3} = I_x (r_{o3} \parallel 1/g_{m3})$$

$$V_{gs4} = -g_{m2} V_{gs2} (r_{o1} \parallel r_{o2}) - V_{gs2}$$

$$\text{or } v_{gs4} = -[1 + g_{m2}(r_{o1} \parallel r_{o2})] v_{gs2}$$

$$= -[1 + g_{m2}(r_{o1} \parallel r_{o2})] v_{sb4}$$

$$\therefore v_{gs4} = -[1 + g_{m2}(r_{o1} \parallel r_{o2})] I_x (r_{o3} \parallel \frac{1}{g_{m3}}) \quad \text{--- (1)}$$

Further

$$I_x = g_{m4} v_{gs4} - g_{mb4} v_{sb4} + \frac{v_x - v_{gs2}}{r_{o4}} \quad \text{--- (2)}$$

From (1) & (2)

$$R_{out} = \frac{v_x}{I_x} = r_{o4} [1 + g_{m4}(r_{o3} \parallel \frac{1}{g_{m3}})] (1 + g_{m2}(r_{o1} \parallel r_{o2}))$$

$$+ g_{mb4} [(r_{o3} \parallel \frac{1}{g_{m3}}) + \frac{1}{r_{o4}} (r_{o3} \parallel \frac{1}{g_{m3}}) r_o]$$



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Assume M_3 & M_4 identical, then

$$g_{m3} = g_{m4}, \quad r_{o3} \parallel \frac{1}{g_{m3}} = \frac{1}{g_{m3}} = \frac{1}{g_{m4}}$$

Further we see $r_o = r_{o1} = r_{o2} = r_{o4}$ can be assumed

$$\therefore R_{out} = r_o \left\{ \left[1 + 1 \cdot \left(1 + \frac{g_{m3} r_o}{2} \right) \right] + \frac{g_{m64} r_o}{g_{m3}} + \frac{1}{r_o g_{m3}} \right\}$$

$$R_{out} \cong r_o + g_{m2} r_o^2 = r_o (1 + g_{m2} r_o)$$

$\therefore R_{out}$ is Boosted due to cascode configuration.

Next thing we wish to know $V_{min} = V_{omin}$

$$\begin{aligned} \text{or } V_{omin} &= V_{GS3} + V_{DS4,sat} \\ &= V_{GS3} + V_{GS4} - V_{T4} \end{aligned}$$



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$$V_{\text{omin}} = \sqrt{\frac{2I_0}{\beta_3}} + V_{T3} + \sqrt{\frac{2I_0}{\beta_4}}$$

If $\beta_3 = \beta_4$, then

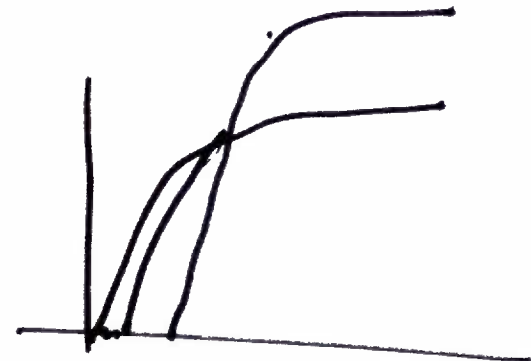
$$V_{\text{omin}} = 2\sqrt{\frac{2I_0}{\beta'(W/L)}} + V_T$$

$$\text{or } V_{\text{omin}} \propto \sqrt{2I_0}$$

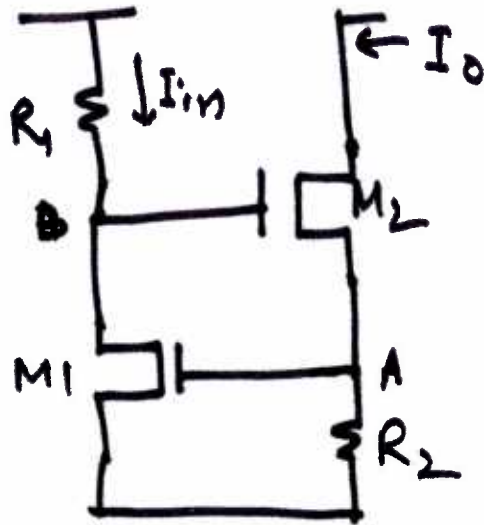


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(iv) V_T reference CS



This is good stable source

If $I_0 \uparrow$, $I_{DS2} = I_{R2}$

also increase. Drop across

R_2 increases ($V_A = I_0 \cdot R_2$) increases

V_{GS1} of M_1 . Hence I_{DS1} increase with increase of I_0 .

Since I_{in} is good current source,

Hence increase in I_{DS1} causes V_B to

reduce. But $V_B = V_{G2}$. Thus

reduction in V_{G2} reduces V_{GS2} which in turn reduces I_0 . Thus Negative feedback leads to Stability



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Clearly $I_0 = I_{DS2} = I_{R2}$

$$\therefore I_0 = \frac{V_A}{R_2} = \frac{V_{GS1}}{R_2}$$

$$\text{or } I_0 = \frac{V_{OV} + V_T}{R_2}$$

$$I_0 = \frac{V_T + \sqrt{\frac{2 I_{in}}{\beta' (W/L)}}}{R_2}$$

Thus I_0 is function of V_T , which is relatively fixed value.



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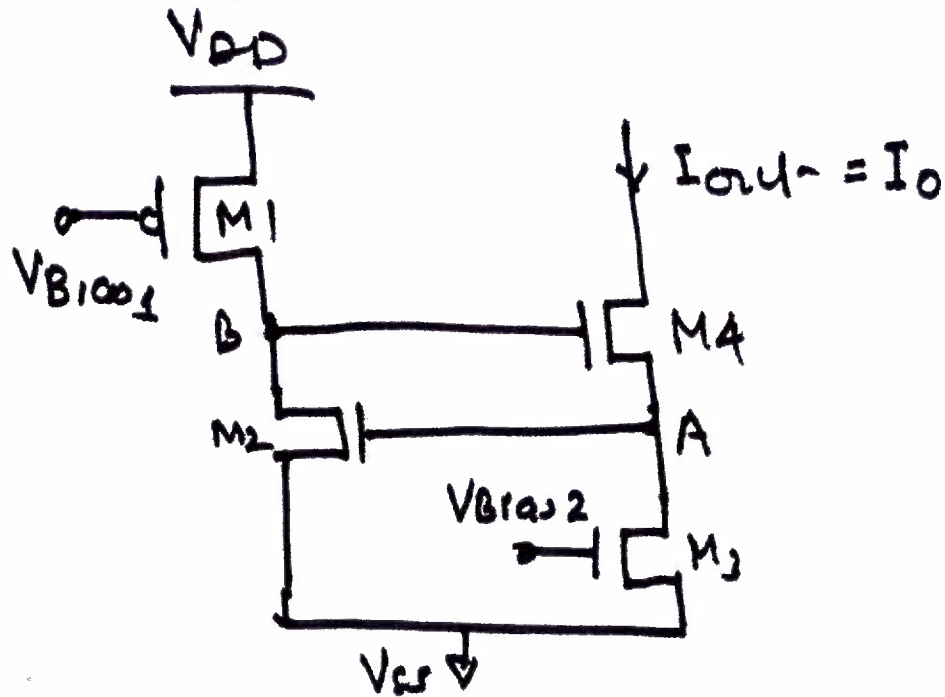
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A Better version of V_T reference CS, is
Regulated Cascode CS.



If we have large
(W/L) for M_2 , then

$$V_{OV} (= V_{GS2} - V_T) \text{ is } \ll V_T$$

$$\therefore I_0 \cong \frac{V_T}{R_2}$$

However if we do Small Signal Analysis

$$R_{out} \cong g_m r_o^2 \left\{ 1 + \frac{1}{2} g_m r_o \right\} \cong \frac{1}{2} g_m^2 r_o^3$$